



**128K x 36, 256K x 18  
3.3V Synchronous SRAMs  
3.3V I/O, Pipelined Outputs  
Burst Counter, Single Cycle Deselect**

**AS8C403600  
AS8C401800**

## Features

- ◆ 128K x 36, 256K x 18 memory configurations
- ◆ Supports high system speed:
  - Commercial:
    - 150MHz 3.8ns clock access time
- ◆ LBO input selects interleaved or linear burst mode
- ◆ Self-timed write cycle with global write control (GW), byte write enable (BWE), and byte writes (BWx)
- ◆ 3.3V core power supply
- ◆ Power down controlled by ZZ input
- ◆ 3.3V I/O
- ◆ Optional - Boundary Scan JTAG Interface (IEEE 1149.1 compliant)
- ◆ Packaged in a JEDEC Standard 100-pin plastic thin quad flatpack (TQFP).

## Description

The AS8C403600/1800 are high-speed SRAMs organized as 128K x 36/256K x 18. The AS8C403600/401800 SRAMs contain write, data, address and control registers. Internal logic allows the SRAM to generate a self-timed write based upon a decision which can be left until the end of the write cycle.

The burst mode feature offers the highest level of performance to the system designer, as the AS8C403600/1800 can provide four cycles of data for a single address presented to the SRAM. An internal burst address counter accepts the first cycle address from the processor, initiating the access sequence. The first cycle of output data will be pipelined for one cycle before it is available on the next rising clock edge. If burst mode operation is selected (ADV=LOW), the subsequent three cycles of output data will be available to the user on the next three rising clock edges. The order of these three addresses are defined by the internal burst counter and the LBO input pin.

The AS8C403600/1800 SRAMs utilize the latest high-performance CMOS process and are packaged in a JEDEC standard 14mm x 20mm 100-pin thin plastic quad flatpack (TQFP).

## Pin Description Summary

A0-A17	Address Inputs	Input	Synchronous
CE	Chip Enable	Input	Synchronous
CS0, CS1	Chip Selects	Input	Synchronous
OE	Output Enable	Input	Asynchronous
GW	Global Write Enable	Input	Synchronous
BWE	Byte Write Enable	Input	Synchronous
BW1, BW2, BW3, BW4 <sup>(1)</sup>	Individual Byte Write Selects	Input	Synchronous
CLK	Clock	Input	N/A
ADV	Burst Address Advance	Input	Synchronous
ADSC	Address Status (Cache Controller)	Input	Synchronous
ADSP	Address Status (Processor)	Input	Synchronous
LBO	Linear / Interleaved Burst Order	Input	DC
TMS	Test Mode Select	Input	Synchronous
TDI	Test Data Input	Input	Synchronous
TCK	Test Clock	Input	N/A
TDO	Test Data Output	Output	Synchronous
ZZ	Sleep Mode	Input	Asynchronous
I/O0-I/O31, I/OP1-I/OP4	Data Input / Output	I/O	Synchronous
Vdd, Vddq	Core Power, I/O Power	Supply	N/A
Vss	Ground	Supply	N/A

### NOTE:

1. BW3 and BW4 are not applicable for the AS8C401800.

**Pin Definitions<sup>(1)</sup>**

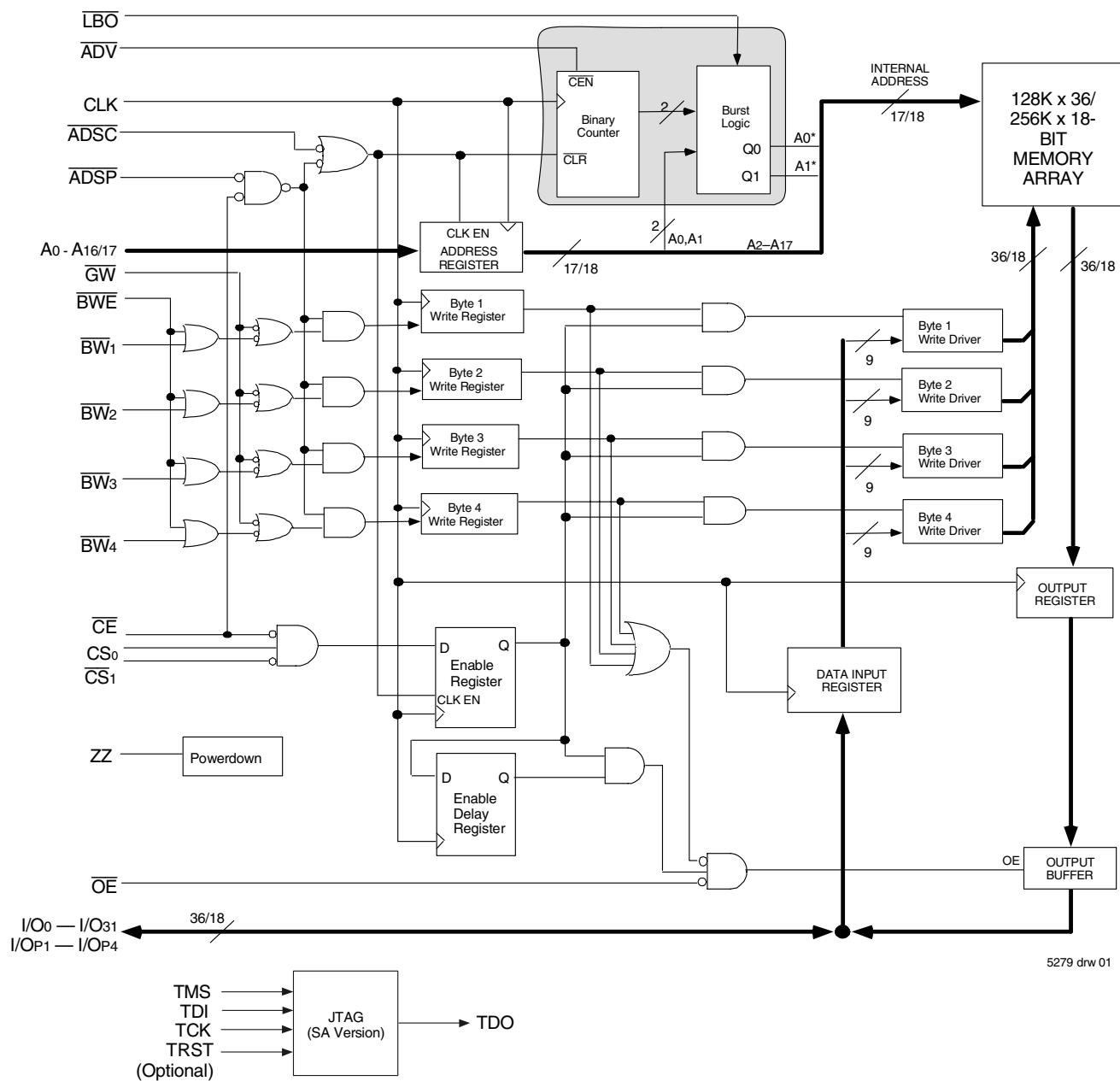
Symbol	Pin Function	I/O	Active	Description
A <sub>0</sub> -A <sub>17</sub>	Address Inputs	I	N/A	Synchronous Address inputs. The address register is triggered by a combination of the rising edge of CLK and $\overline{ADSC}$ Low or $\overline{ADSP}$ Low and $\overline{CE}$ Low.
$\overline{ADSC}$	Address Status (Cache Controller)	I	LOW	Synchronous Address Status from Cache Controller. $\overline{ADSC}$ is an active LOW input that is used to load the address registers with new addresses.
$\overline{ADSP}$	Address Status (Processor)	I	LOW	Synchronous Address Status from Processor. $\overline{ADSP}$ is an active LOW input that is used to load the address registers with new addresses. $\overline{ADSP}$ is gated by $\overline{CE}$ .
$\overline{ADV}$	Burst Address Advance	I	LOW	Synchronous Address Advance. $\overline{ADV}$ is an active LOW input that is used to advance the internal burst counter, controlling burst access after the initial address is loaded. When the input is HIGH the burst counter is not incremented; that is, there is no address advance.
$\overline{BWE}$	Byte Write Enable	I	LOW	Synchronous byte write enable gates the byte write inputs $\overline{BW}_1$ - $\overline{BW}_4$ . If $\overline{BWE}$ is LOW at the rising edge of CLK then $\overline{BW}_x$ inputs are passed to the next stage in the circuit. If $\overline{BWE}$ is HIGH then the byte write inputs are blocked and only $\overline{GW}$ can initiate a write cycle.
$\overline{BW}_1$ - $\overline{BW}_4$	Individual Byte Write Enables	I	LOW	Synchronous byte write enables. $\overline{BW}_1$ controls I/O <sub>0</sub> - <sub>7</sub> , I/O <sub>1</sub> , $\overline{BW}_2$ controls I/O <sub>8</sub> - <sub>15</sub> , I/O <sub>2</sub> , etc. Any active byte write causes all outputs to be disabled.
$\overline{CE}$	Chip Enable	I	LOW	Synchronous chip enable. $\overline{CE}$ is used with CS <sub>0</sub> and CS <sub>1</sub> to enable the AS8C403600/1800. $\overline{CE}$ also gates ADSP.
CLK	Clock	I	N/A	This is the clock input. All timing references for the device are made with respect to this input.
CS <sub>0</sub>	Chip Select 0	I	HIGH	Synchronous active HIGH chip select. CS <sub>0</sub> is used with $\overline{CE}$ and CS <sub>1</sub> to enable the chip.
CS <sub>1</sub>	Chip Select 1	I	LOW	Synchronous active LOW chip select. CS <sub>1</sub> is used with $\overline{CE}$ and CS <sub>0</sub> to enable the chip.
$\overline{GW}$	Global Write Enable	I	LOW	Synchronous global write enable. This input will write all four 9-bit data bytes when LOW on the rising edge of CLK. $\overline{GW}$ supersedes individual byte write enables.
I/O <sub>0</sub> -I/O <sub>31</sub> I/O <sub>1</sub> -I/O <sub>4</sub>	Data Input/Output	I/O	N/A	Synchronous data input/output (I/O) pins. Both the data input path and data output path are registered and triggered by the rising edge of CLK.
$\overline{LBO}$	Linear Burst Order	I	LOW	Asynchronous burst order selection input. When $\overline{LBO}$ is HIGH, the interleaved burst sequence is selected. When $\overline{LBO}$ is LOW the Linear burst sequence is selected. $\overline{LBO}$ is a static input and must not change state while the device is operating.
$\overline{OE}$	Output Enable	I	LOW	Asynchronous output enable. When $\overline{OE}$ is LOW the data output drivers are enabled on the I/O pins if the chip is also selected. When $\overline{OE}$ is HIGH the I/O pins are in a high-impedance state.
TMS	Test Mode Select	I	N/A	Gives input command for TAP controller. Sampled on rising edge of TCK. This pin has an internal pullup.
TDI	Test Data Input	I	N/A	Serial input of registers placed between TDI and TDO. Sampled on rising edge of TCK. This pin has an internal pullup.
TCK	Test Clock	I	N/A	Clock input of TAP controller. Each TAP event is clocked. Test inputs are captured on rising edge of TCK, while test outputs are driven from the falling edge of TCK. This pin has an internal pullup.
TDO	Test Data Output	O	N/A	Serial output of registers placed between TDI and TDO. This output is active depending on the state of the TAP controller.
ZZ	Sleep Mode	I	HIGH	Asynchronous sleep mode input. ZZ HIGH will gate the CLK internally and power down the AS8C403600/1800 to its lowest power consumption level. Data retention is guaranteed in Sleep Mode. This pin has an internal pull down.
V <sub>DD</sub>	Power Supply	N/A	N/A	3.3V core power supply.
V <sub>DDQ</sub>	Power Supply	N/A	N/A	3.3V I/O Supply.
V <sub>SS</sub>	Ground	N/A	N/A	Ground.
NC	No Connect	N/A	N/A	NC pins are not electrically connected to the device.

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**NOTE:**

- All synchronous inputs must meet specified setup and hold times with respect to CLK.

## Functional Block Diagram



**Absolute Maximum Ratings<sup>(1)</sup>**

Symbol	Rating	Commercial & Industrial	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
VTERM <sup>(3,6)</sup>	Terminal Voltage with Respect to GND	-0.5 to VDD	V
VTERM <sup>(4,6)</sup>	Terminal Voltage with Respect to GND	-0.5 to VDD +0.5	V
VTERM <sup>(5,6)</sup>	Terminal Voltage with Respect to GND	-0.5 to VDDQ +0.5	V
TA <sup>(7)</sup>	Commercial Operating Temperature	-0 to +70	°C
	Industrial Operating Temperature	-40 to +85	°C
TBIAS	Temperature Under Bias	-55 to +125	°C
TSTG	Storage Temperature	-55 to +125	°C
PT	Power Dissipation	2.0	W
IOUT	DC Output Current	50	mA

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. VDD terminals only.
3. VDDQ terminals only.
4. Input terminals only.
5. I/O terminals only.
6. This is a steady-state DC parameter that applies after the power supplies have ramped up. Power supply sequencing is not necessary; however, the voltage on any input or I/O pin cannot exceed VDDQ during power supply ramp up.
7. TA is the "instant on" case temperature.

**Recommended Operating Temperature and Supply Voltage**

Grade	Temperature <sup>(1)</sup>	Vss	VDD	VDDQ
Commercial	0°C to +70°C	0V	3.3V±5%	3.3V±5%
Industrial	-40°C to +85°C	0V	3.3V±5%	3.3V±5%

NOTES:

1. TA is the "instant on" case temperature.

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**Recommended DC Operating Conditions**

Symbol	Parameter	Min.	Typ.	Max.	Unit
VDD	Core Supply Voltage	3.135	3.3	3.465	V
VDDQ	I/O Supply Voltage	3.135	3.3	3.465	V
Vss	Supply Voltage	0	0	0	V
VIH	Input High Voltage - Inputs	2.0	—	VDD +0.3	V
VIH	Input High Voltage - I/O	2.0	—	VDDQ +0.3 <sup>(1)</sup>	V
VIL	Input Low Voltage	-0.3 <sup>(2)</sup>	—	0.8	V

5279tbl 06

NOTES:

1. VIH (max) = V DDQ + 1.0V for pulse width less than tCYC/2, once per cycle.
2. VIL (min) = -1.0V for pulse width less than tCYC/2, once per cycle.

**100 Pin TQFP Capacitance  
(TA = +25°C, f = 1.0MHz)**

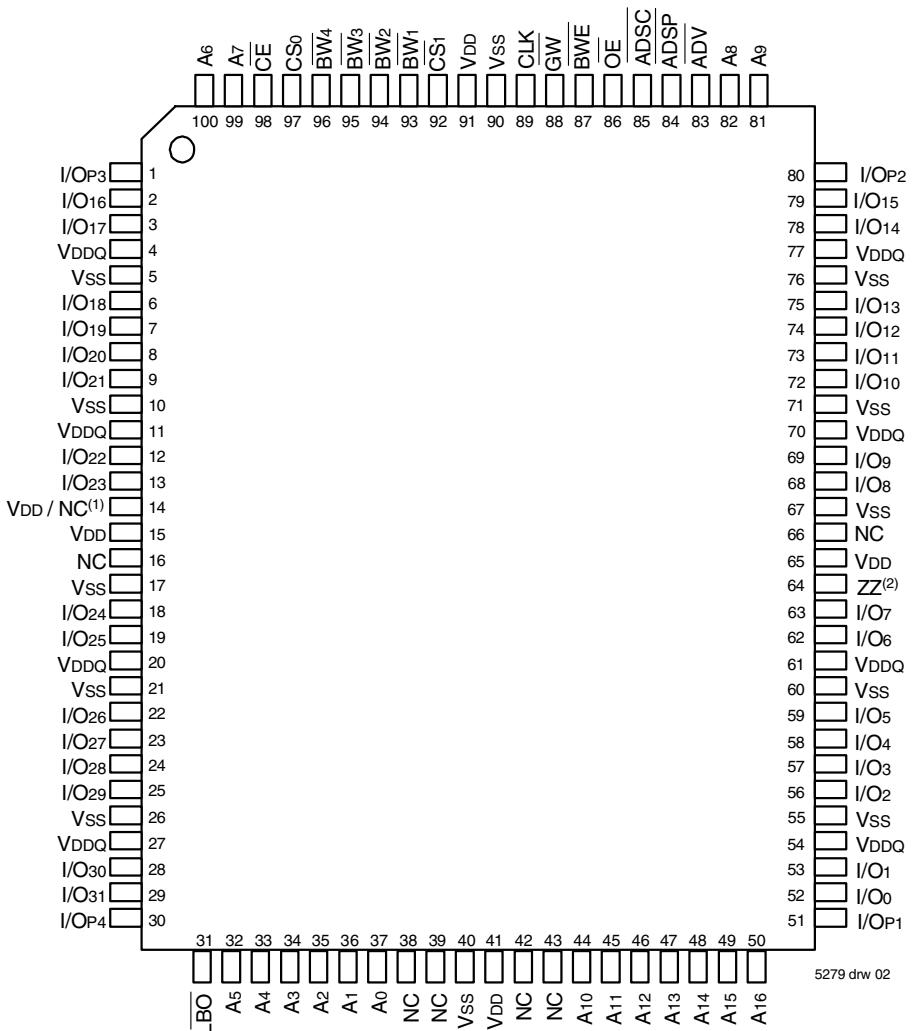
Symbol	Parameter <sup>(1)</sup>	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	5	pF
CIO	I/O Capacitance	VOUT = 3dV	7	pF

NOTE:

1. This parameter is guaranteed by device characterization, but not production tested.

5279tbl 07

## Pin Configuration – 128K x 36

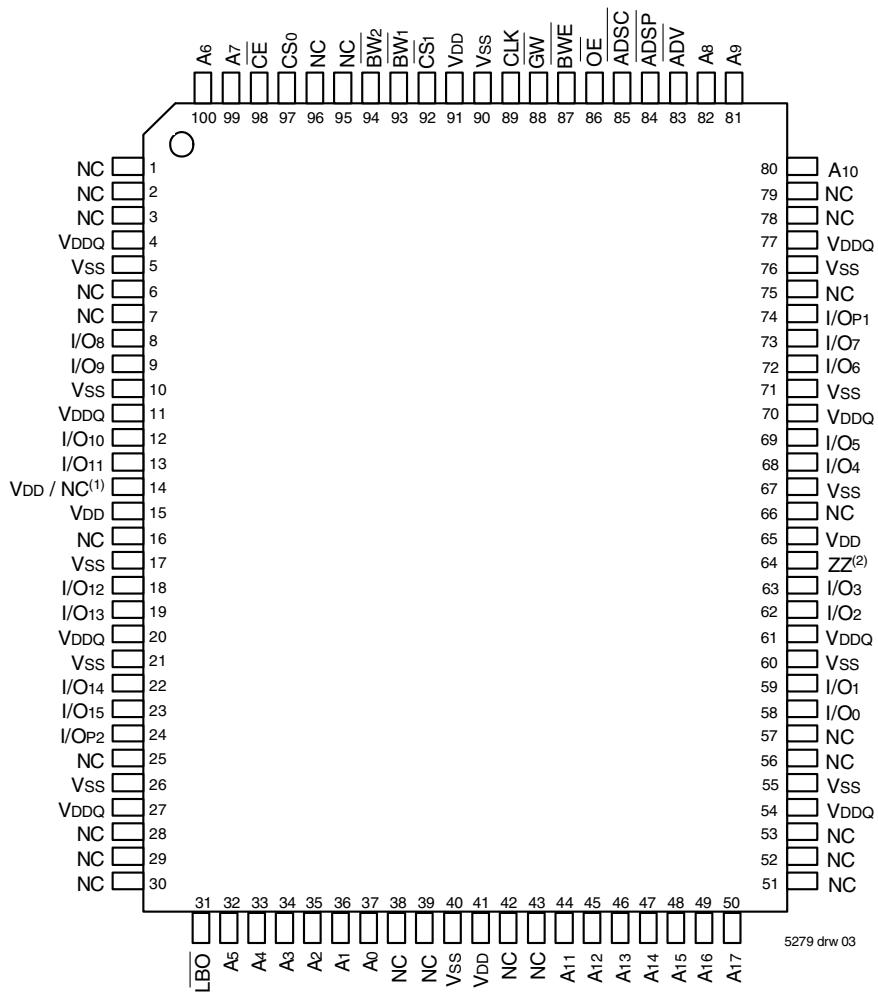


**TQFP  
Top View**

### NOTES:

1. Pin 14 can either be directly connected to V<sub>DD</sub>, or connected to an input voltage  $\geq V_{IH}$ , or left unconnected.
2. Pin 64 can be left unconnected and the device will always remain in active mode.

## Pin Configuration – 256K x 18



**TQFP**  
**Top View**

### NOTES:

1. Pin 14 can either be directly connected to V<sub>DD</sub>, or connected to an input voltage  $\geq V_{IH}$ , or left unconnected.
2. Pin 64 can be left unconnected and the device will always remain in active mode.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ( $V_{DD} = 3.3V \pm 5\%$ )

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
$ I_L $	Input Leakage Current	$V_{DD} = \text{Max.}$ , $V_{IN} = 0V$ to $V_{DD}$	—	5	$\mu A$
$ I_{LZ} $	$ZZ$ , $\overline{LBO}$ and JTAG Input Leakage Current <sup>(1)</sup>	$V_{DD} = \text{Max.}$ , $V_{IN} = 0V$ to $V_{DD}$	—	30	$\mu A$
$ I_O $	Output Leakage Current	$V_{OUT} = 0V$ to $V_{DDQ}$ , Device Deselected	—	5	$\mu A$
$V_{OL}$	Output Low Voltage	$I_{OL} = +8mA$ , $V_{DD} = \text{Min.}$	—	0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -8mA$ , $V_{DD} = \text{Min.}$	2.4	—	V

5279 tbl 08

NOTE:

- The  $\overline{LBO}$ , TMS, TDI, TCK and  $\overline{TRST}$  pins will be internally pulled to  $V_{DD}$  and the  $ZZ$  pin will be internally pulled to  $V_{SS}$  if they are not actively driven in the application.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup>

Symbol	Parameter	Test Conditions	150MHz		133MHz		Unit
			Com'l	Ind	Com'l	Ind	
$I_{DD}$	Operating Power Supply Current	Device Selected, Outputs Open, $V_{DD} = \text{Max.}$ , $V_{DDQ} = \text{Max.}$ , $V_{IN} \geq V_{IH}$ or $\leq V_{IL}$ , $f = f_{MAX}^{(2)}$	295	305	250	260	mA
$I_{SB1}$	CMOS Standby Power Supply Current	Device Deselected, Outputs Open, $V_{DD} = \text{Max.}$ , $V_{DDQ} = \text{Max.}$ , $V_{IN} \geq V_{HD}$ or $\leq V_{LD}$ , $f = 0^{(2,3)}$	30	35	30	35	mA
$I_{SB2}$	Clock Running Power Supply Current	Device Deselected, Outputs Open, $V_{DD} = \text{Max.}$ , $V_{DDQ} = \text{Max.}$ , $V_{IN} \geq V_{HD}$ or $\leq V_{LD}$ , $f = f_{MAX}^{(2,3)}$	105	115	100	110	mA
$I_{zz}$	Full Sleep Mode Supply Current	$ZZ \geq V_{HD}$ , $V_{DD} = \text{Max.}$	30	35	30	35	mA

5279 tbl 09

NOTES:

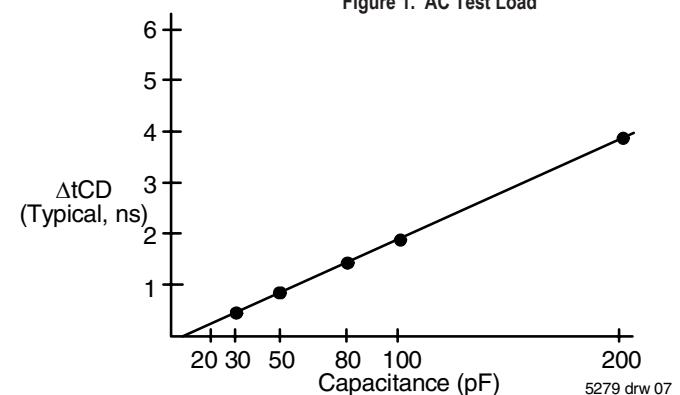
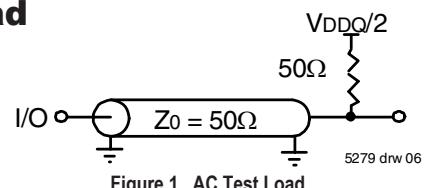
- All values are maximum guaranteed values.
- At  $f = f_{MAX}$ , inputs are cycling at the maximum frequency of read cycles of 1/Tcyc while  $\overline{ADSC} = \text{LOW}$ ;  $f=0$  means no input lines are changing.
- For I/Os  $V_{HD} = V_{DDQ} - 0.2V$ ,  $V_{LD} = 0.2V$ . For other inputs  $V_{HD} = V_{DD} - 0.2V$ ,  $V_{LD} = 0.2V$ .

## AC Test Conditions ( $V_{DDQ} = 3.3V$ )

Input Pulse Levels	0 to 3V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	1.5V
Output Timing Reference Levels	1.5V
AC Test Load	See Figure 1

5279 tbl 10

## AC Test Load



### Synchronous Truth Table<sup>(1,3)</sup>

Operation	Address Used	$\overline{CE}$	$CS_0$	$CS_1$	$ADSP$	$ADSC$	$ADV$	$GW$	$BWE$	$BWx$	$\overline{OE}$ (2)	$CLK$	I/O
Deselected Cycle, over Power Down	None	H	X	X	X	L	X	X	X	X	X	-	Hi-Z
Deselected Cycle, over Power Down	None	L	X	H	L	X	X	X	X	X	X	-	Hi-Z
Deselected Cycle, over Power Down	None	L	L	X	L	X	X	X	X	X	X	-	Hi-Z
Deselected Cycle, over Power Down	None	L	X	H	X	L	X	X	X	X	X	-	Hi-Z
Deselected Cycle, over Power Down	None	L	L	X	X	L	X	X	X	X	X	-	Hi-Z
Read Cycle, Begin Burst	External	L	H	L	L	X	X	X	X	X	L	-	DOUT
Read Cycle, Begin Burst	External	L	H	L	L	X	X	X	X	X	H	-	Hi-Z
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	H	X	L	-	DOUT
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	H	L	-	DOUT
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	H	H	-	Hi-Z
Write Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	L	X	-	DIN
Write Cycle, Begin Burst	External	L	H	L	H	L	X	L	X	X	X	-	DIN
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	H	X	L	-	DOUT
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	H	X	H	-	Hi-Z
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	X	H	L	-	DOUT
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	X	H	H	-	Hi-Z
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	L	-	DOUT
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	-	Hi-Z
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	X	H	H	-	DOUT
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	X	H	H	-	Hi-Z
Write Cycle, Continue Burst	Next	X	X	X	H	H	L	H	L	L	X	-	DIN
Write Cycle, Continue Burst	Next	X	X	X	H	H	L	H	L	X	X	-	DIN
Write Cycle, Continue Burst	Next	H	X	X	X	H	L	H	L	L	X	-	DIN
Write Cycle, Continue Burst	Next	H	X	X	X	H	L	H	L	X	X	-	DIN
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	H	X	L	-	DOUT
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	H	X	H	-	Hi-Z
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	X	H	L	-	DOUT
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	X	H	H	-	Hi-Z
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	L	-	DOUT
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	-	Hi-Z
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	-	DOUT
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	-	Hi-Z
Write Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	L	L	X	-	DIN
Write Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	L	X	X	-	DIN
Write Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	L	X	-	DIN
Write Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	L	X	-	DIN

NOTES:

1. L = V<sub>IL</sub>, H = V<sub>IH</sub>, X = Don't Care.
2.  $\overline{OE}$  is an asynchronous input.
3. ZZ = low for this table.

5279 tbl 11

### Synchronous Write Function Truth Table<sup>(1, 2)</sup>

Operation	$\overline{GW}$	$BWE$	$\overline{BW}_1$	$\overline{BW}_2$	$\overline{BW}_3$	$\overline{BW}_4$
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write all Bytes	L	X	X	X	X	X
Write all Bytes	H	L	L	L	L	L
Write Byte 1 <sup>(3)</sup>	H	L	L	H	H	H
Write Byte 2 <sup>(3)</sup>	H	L	H	L	H	H
Write Byte 3 <sup>(3)</sup>	H	L	H	H	L	H
Write Byte 4 <sup>(3)</sup>	H	L	H	H	H	L

5279 tbl 12

**NOTES:**

1. L = V<sub>IL</sub>, H = V<sub>IH</sub>, X = Don't Care.
2.  $\overline{BW}_3$  and  $\overline{BW}_4$  are not applicable for the AS8C401800.
3. Multiple bytes may be selected during the same cycle.

### Asynchronous Truth Table<sup>(1)</sup>

Operation <sup>(2)</sup>	$\overline{OE}$	$\overline{Z}$	I/O Status	Power
Read	L	L	Data Out	Active
Read	H	L	High-Z	Active
Write	X	L	High-Z – Data In	Active
Deselected	X	L	High-Z	Standby
Sleep Mode	X	H	High-Z	Sleep

5279 tbl 13

**NOTES:**

1. L = V<sub>IL</sub>, H = V<sub>IH</sub>, X = Don't Care.
2. Synchronous function pins must be biased appropriately to satisfy operation requirements.

### Interleaved Burst Sequence Table ( $\overline{LBO}=\overline{VDD}$ )

	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	0	0	1	1	1	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address <sup>(1)</sup>	1	1	1	0	0	1	0	0

5279 tbl 14

**NOTE:**

1. Upon completion of the Burst sequence the counter wraps around to its initial state.

### Linear Burst Sequence Table ( $\overline{LBO}=\overline{Vss}$ )

	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	1	0	1	1	0	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address <sup>(1)</sup>	1	1	0	0	0	1	1	0

5279 tbl 15

**NOTE:**

1. Upon completion of the Burst sequence the counter wraps around to its initial state.

**AC Electrical Characteristics**(V<sub>DD</sub> = 3.3V ±5%, Commercial and Industrial Temperature Ranges)

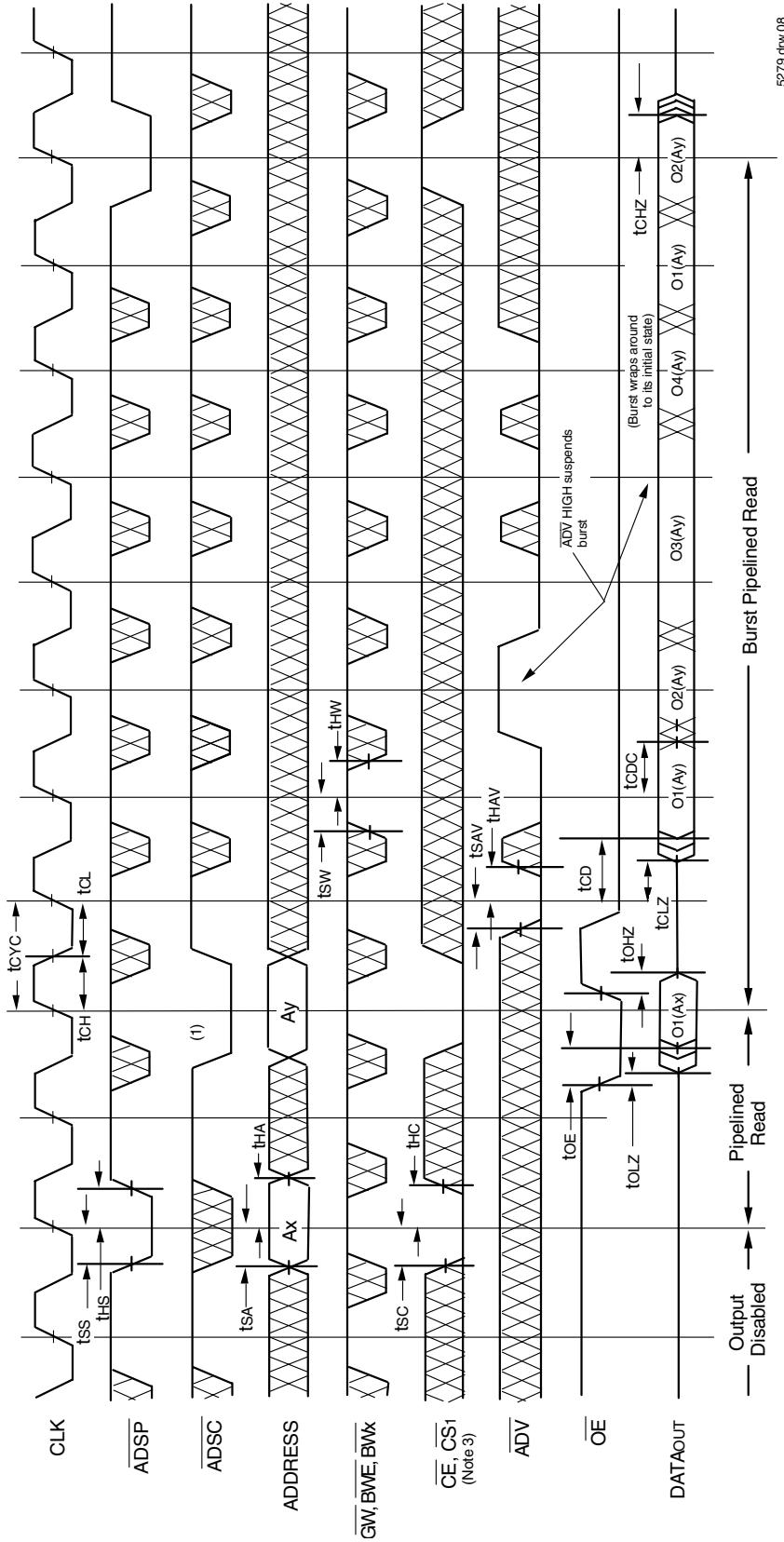
Symbol	Parameter	150MHz		133MHz		Unit
		Min.	Max.	Min.	Max.	
t <sub>CYC</sub>	Clock Cycle Time	6.7	—	7.5	—	ns
t <sub>CH</sub> <sup>(1)</sup>	Clock High Pulse Width	2.6	—	3	—	ns
t <sub>CL</sub> <sup>(1)</sup>	Clock Low Pulse Width	2.6	—	3	—	ns
<b>Output Parameters</b>						
t <sub>CD</sub>	Clock High to Valid Data	—	3.8	—	4.2	ns
t <sub>ODC</sub>	Clock High to Data Change	1.5	—	1.5	—	ns
t <sub>AZ</sub> <sup>(2)</sup>	Clock High to Output Active	0	—	0	—	ns
t <sub>CHZ</sub> <sup>(2)</sup>	Clock High to Data High-Z	1.5	3.8	1.5	4.2	ns
t <sub>OE</sub>	Output Enable Access Time	—	3.8	—	4.2	ns
t <sub>OLZ</sub> <sup>(2)</sup>	Output Enable Low to Output Active	0	—	0	—	ns
t <sub>OHZ</sub> <sup>(2)</sup>	Output Enable High to Output High-Z	—	3.8	—	4.2	ns
<b>Set Up Times</b>						
t <sub>SA</sub>	Address Setup Time	1.5	—	1.5	—	ns
t <sub>SS</sub>	Address Status Setup Time	1.5	—	1.5	—	ns
t <sub>SD</sub>	Data In Setup Time	1.5	—	1.5	—	ns
t <sub>SW</sub>	Write Setup Time	1.5	—	1.5	—	ns
t <sub>SADV</sub>	Address Advance Setup Time	1.5	—	1.5	—	ns
t <sub>SC</sub>	Chip Enable/Select Setup Time	1.5	—	1.5	—	ns
<b>Hold Times</b>						
t <sub>HA</sub>	Address Hold Time	0.5	—	0.5	—	ns
t <sub>HS</sub>	Address Status Hold Time	0.5	—	0.5	—	ns
t <sub>HD</sub>	Data In Hold Time	0.5	—	0.5	—	ns
t <sub>HW</sub>	Write Hold Time	0.5	—	0.5	—	ns
t <sub>HADV</sub>	Address Advance Hold Time	0.5	—	0.5	—	ns
t <sub>HC</sub>	Chip Enable/Select Hold Time	0.5	—	0.5	—	ns
<b>Sleep Mode and Configuration Parameters</b>						
t <sub>ZPW</sub>	ZZ Pulse Width	100	—	100	—	ns
t <sub>ZR</sub> <sup>(3)</sup>	ZZ Recovery Time	100	—	100	—	ns
t <sub>CFG</sub> <sup>(4)</sup>	Configuration Set-up Time	27	—	30	—	ns

**NOTES:**

1. Measured as HIGH above V<sub>IH</sub> and LOW below V<sub>IL</sub>.
2. Transition is measured ±200mV from steady-state.
3. Device must be deselected when powered-up from sleep mode.
4. t<sub>CFG</sub> is the minimum time required to configure the device based on the LBO input. LBO is a static input and must not change during normal operation.

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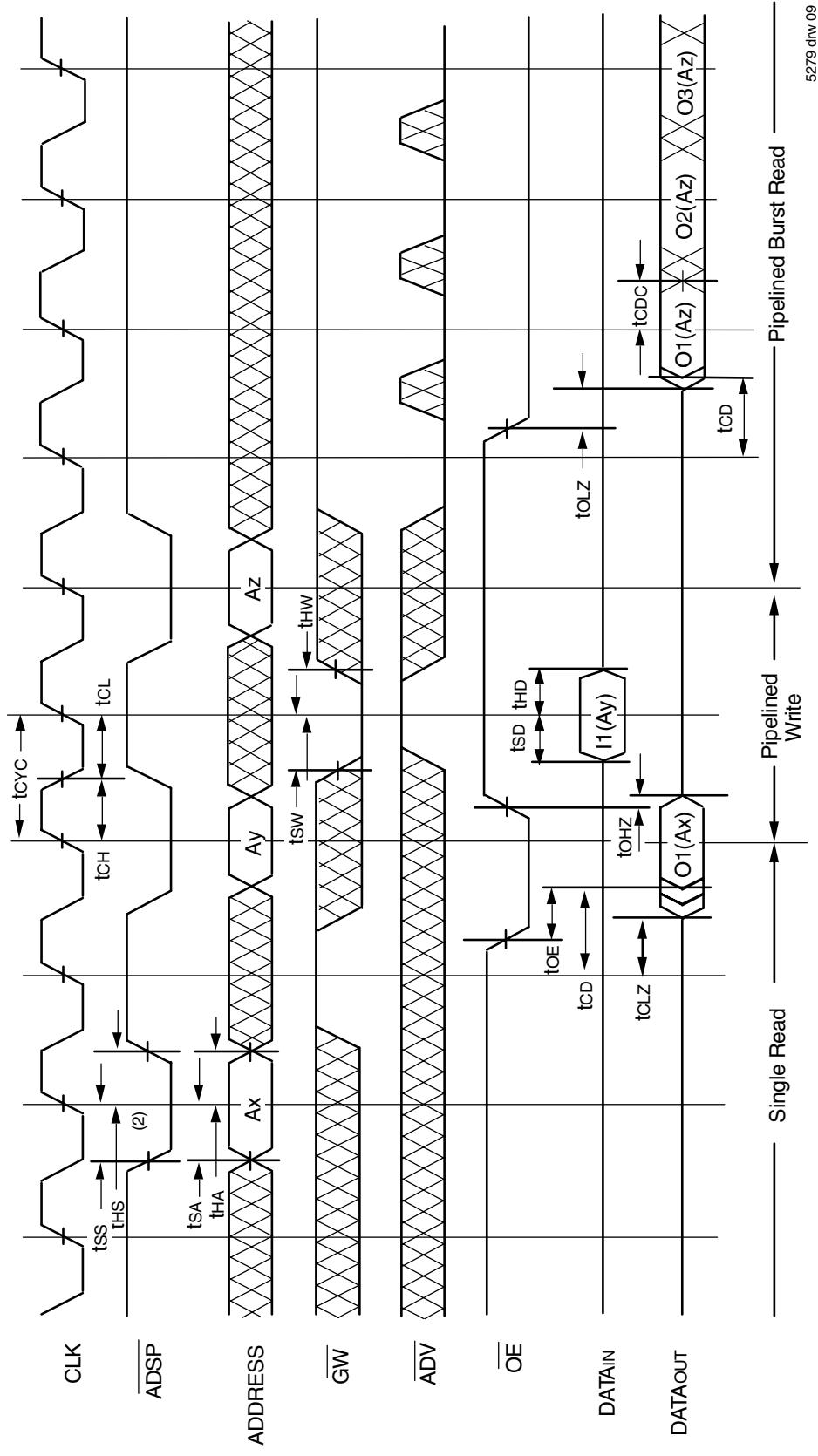
## Timing Waveform of Pipelined Read Cycle<sup>(1,2)</sup>



### NOTES:

1. O1 (Ax) represents the first output from the external address Ax. O1 (Ay) represents the next output data in the burst sequence of the base address Ay, etc. where A0 and A1 are advancing for the four word burst in the sequence defined by the state of the  $\overline{LBO}$  input.
2. ZZ input is LOW and  $\overline{LBO}$  Don't Care for this cycle.
3. CS0 timing transitions are identical but inverted to the  $\overline{CE}$  and  $\overline{CS1}$  signals. For example, when  $\overline{CE}$  and  $\overline{CS1}$  are LOW on this waveform, CS 0 is HIGH.

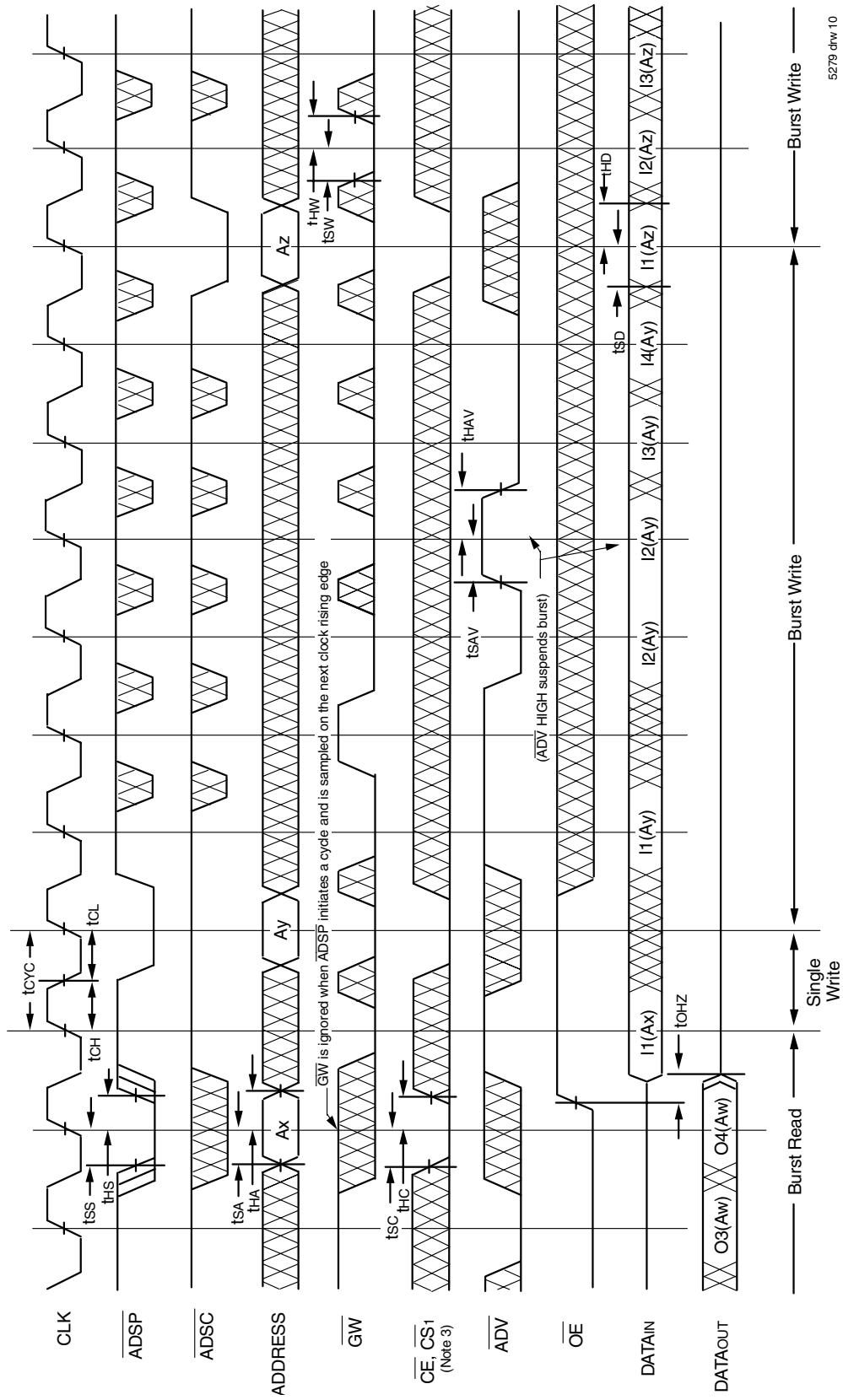
## Timing Waveform of Combined Pipelined Read and Write Cycles<sup>(1,2,3)</sup>



### NOTES:

1. Device is selected through entire cycle;  $\overline{CE}$  and  $\overline{CS}_1$  are LOW, CS<sub>0</sub> is HIGH.
2. ZZ input is LOW and  $\overline{LBO}$  is Don't Care for this cycle.
3. O1 (Ax) represents the first output from the external address Ax; O2 (Az) represents the next output data in the burst sequence of the base address Az, etc. where A0 and A1 are advancing for the four word burst; n in the sequence defined by the state of the  $\overline{LBO}$  input.

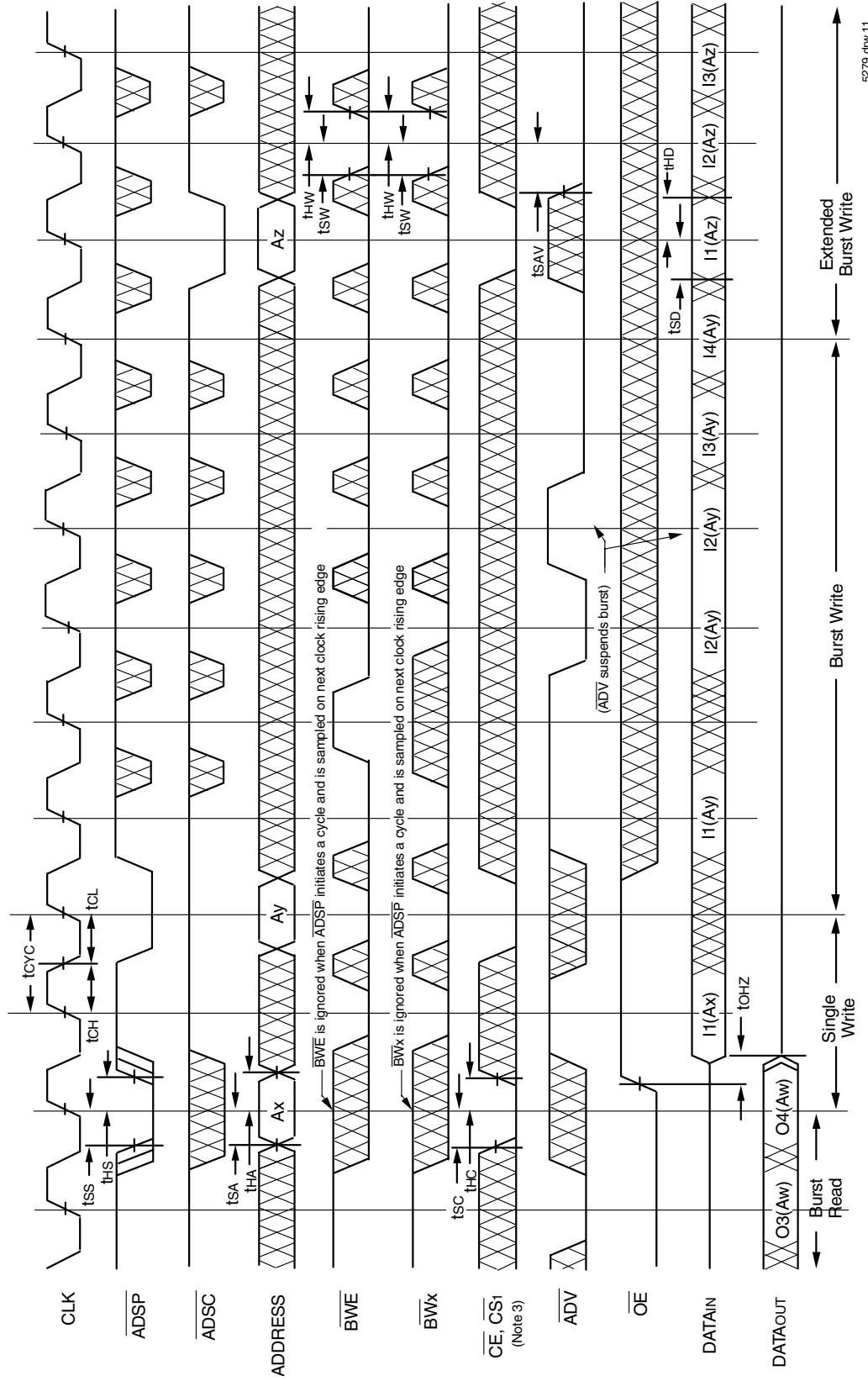
## Timing Waveform of Write Cycle No. 1 - $\overline{\text{GW}}$ Controlled<sup>(1,2,3)</sup>



### NOTES:

1. ZZ input is LOW,  $\overline{\text{BWE}}$  is HIGH and  $\overline{\text{EO}}$  is Don't Care for this cycle.
2. O4 (Aw) represents the final output data in the burst sequence of the base address Aw. I1 (Ay) represents the first input the external address Aw. I1 (Ay) represents the first input from the external address Ay; I2 (Ay) represents the next input data in the burst sequence of the base address Ay, etc. where A0 and A1 are advancing for the four word burst in the sequence defined by the state of the  $\overline{\text{LBW}}$  input. In the case of input I2 (Ay) this data is valid for two cycles because  $\overline{\text{ADV}}$  is high and has suspended the burst.
3. CS0 timing transitions are identical but inverted to the  $\overline{\text{CE}}$  and  $\overline{\text{CS}}_1$  signals. For example, when  $\overline{\text{CE}}$  and  $\overline{\text{CS}}_1$  are LOW on this waveform, CS0 is HIGH.

## Timing Waveform of Write Cycle No. 2 - Byte Controlled<sup>(1,2,3)</sup>

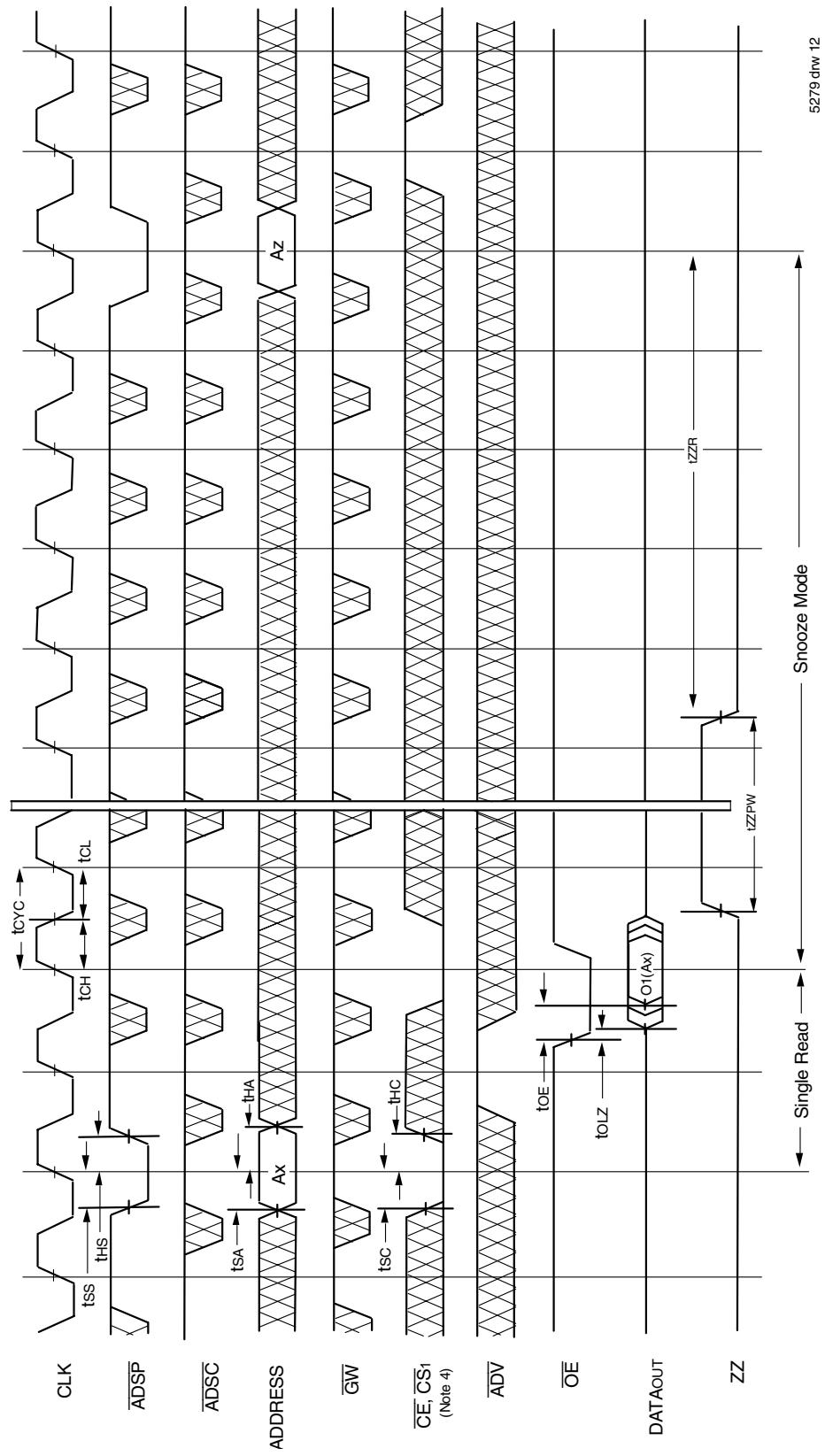


### NOTES:

1. ZZ input is LOW,  $\overline{GW}$  is HIGH and  $\overline{BO}$  is Don't Care for this cycle.
2. O4 (Aw) represents the final output data in the burst sequence of the base address Aw. I1 (Ax) represents the first input external address Ax. I1 (Ay) represents the first input address Ay, etc. where A0 and A1 are advancing for the four word burst in the sequence defined by the state of the  $\overline{BO}$  input. In the case of input I2 (Ay) this data is valid for two cycles because  $\overline{ADV}$  is high and has suspended the burst.
3. CS0 timing transitions are identical but inverted to the  $\overline{CE}$  and  $\overline{CS1}$  signals. For example, when  $\overline{CE}$  and  $\overline{CS1}$  are LOW on this waveform, CS0 is HIGH.

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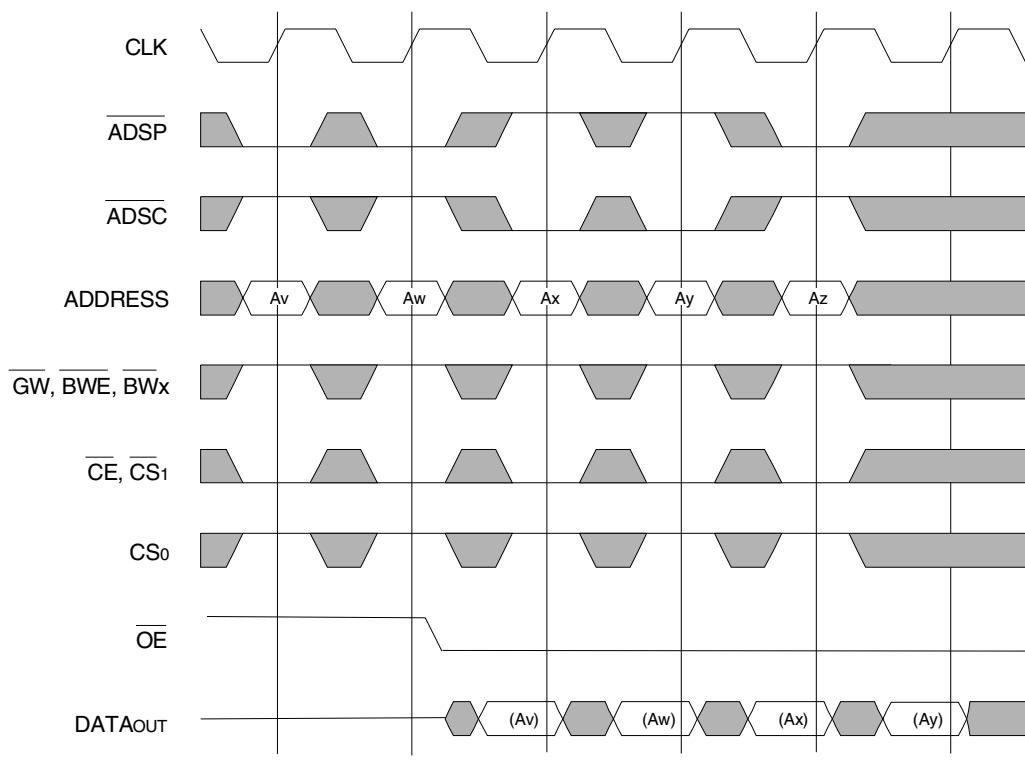
## Timing Waveform of Sleep (ZZ) and Power-Down Modes<sup>(1,2,3)</sup>



### NOTES:

1. Device must power up in deselected Mode
2.  $\overline{LBO}$  is Don't Care for this cycle.
3. It is not necessary to retain the state of the input registers throughout the Power-down cycle.
4. CS<sub>0</sub> timing transitions are identical but inverted to the  $\overline{CE}$  and  $\overline{CS}_1$  signals. For example, when CE and CS<sub>1</sub> are LOW on this waveform, CS<sub>0</sub> is HIGH.

## Non-Burst Read Cycle Timing Waveform

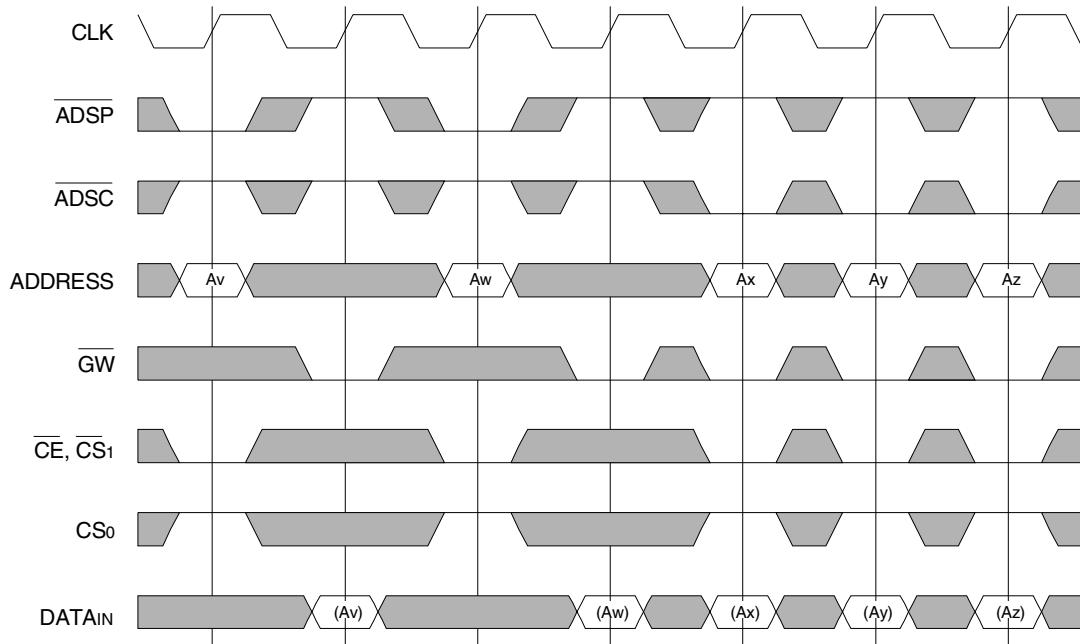


### NOTES:

1. ZZ input is LOW,  $\overline{ADV}$  is HIGH and  $\overline{LBO}$  is Don't Care for this cycle.
2. (Ax) represents the data for address Ax, etc.
3. For read cycles,  $\overline{ADSP}$  and  $\overline{ADSC}$  function identically and are therefore interchangeable.

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## Non-Burst Write Cycle Timing Waveform



### NOTES:

1. ZZ input is LOW,  $\overline{ADV}$  and  $\overline{OE}$  are HIGH, and  $\overline{LBO}$  is Don't Care for this cycle.
2. (Ax) represents the data for address Ax, etc.
3. Although only  $\overline{GW}$  writes are shown, the functionality of  $\overline{BWE}$  and  $\overline{BWx}$  together is the same as  $\overline{GW}$ .
4. For write cycles,  $\overline{ADSP}$  and  $\overline{ADSC}$  have different limitations.

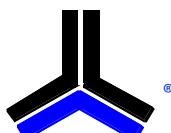
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## **ORDERING INFORMATION**

Alliance	Organization	VCC Range	Package	Operating Temp	Speed Mhz
AS8C403600-QC150N	128K x 36	3.1 - 3.4V	100 pin TQFP	Commercial: 0 C - 70C	150
AS8C401800-QC150N	256K x 18	3.1 - 3.4V	100 pin TQFP	Commercial: 0 C - 70C	150

## **PART NUMBERING SYSTEM**

AS8C	Device	Conf.	Mode	Package	Operating Temp	Speed	N
Sync. SRAM prefix	40 = ( M	18= x18 36 = x36	01= ZBT 00 = Pipelined 25 = Flow- Thru	Q = 100 Pin TQFP	0 ~ 70C	150MHz	N= Leadfree



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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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